

HSB285S

Silicon Schottky Barrier Diode for High frequency detection

REJ03G0010-0100Z Rev.1.00 Apr,16.2003

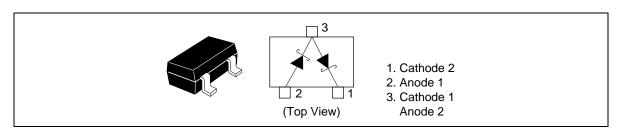
Features

- Low forward voltage, Low capacitance and High detection sensitivity.
- HSB285S which is interconnected in series configuration. is designed for voltage doubler use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB285S	S3	CMPAK

Pin Arrangement



HSB285S

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Value	Unit
Reverse voltage	V_R	2	V
Average rectified current	I ₀ *1	5	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: 1. Per one device

Electrical Characteristics *1

 $(Ta = 25^{\circ}C)$

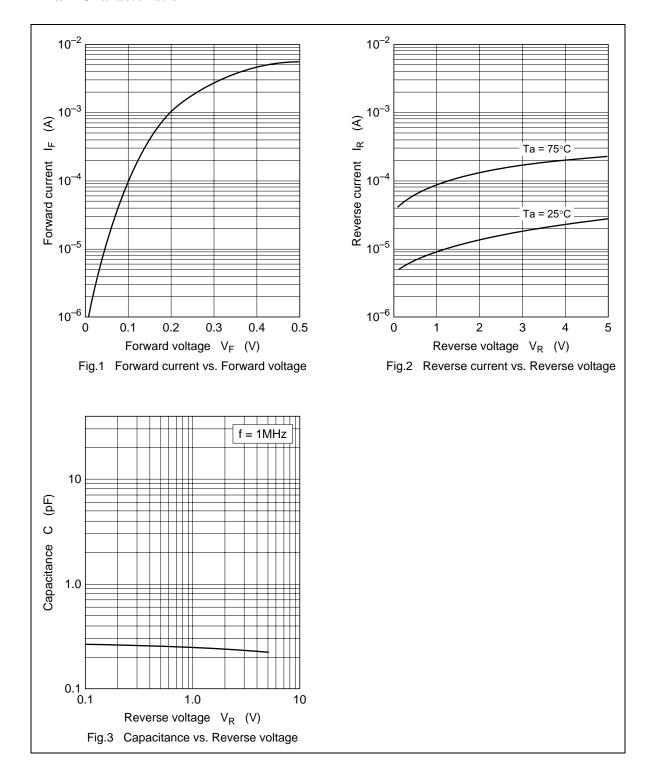
Item	Symbol	Min	Тур	Max	Unit	Test Condition
Forward voltage	V _{F1}	_	_	0.15	V	$I_{\rm F} = 0.1 \text{mA}$
	V_{F2}	_		0.27		I _F = 1 mA
Capacitance	С	_	0.3	_	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
ESD-Capability *2	_	10	_	_	V	$C = 200 \text{ pF}, R_L = 0 \Omega,$
						Both forward and reverse direction 1 pulse.

Notes: 1. Per one device

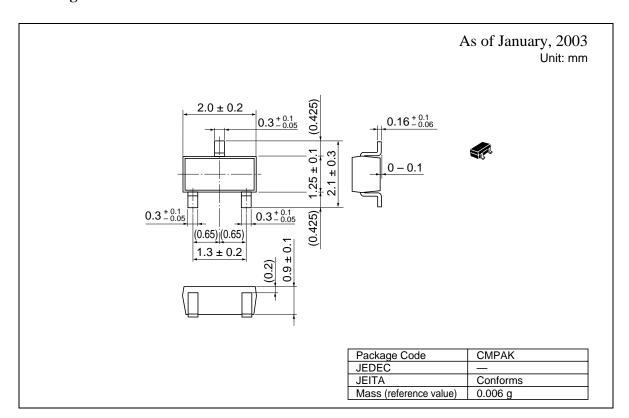
2. Failure criterion ; $I_{\text{R}} \geq 100~\mu\text{A}$ at $V_{\text{R}} = 0.5~\text{V}$

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Main Characteristic



Package Dimensions



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